

116	GaAs P++			
115	$\text{Al}_{x_1}\text{Ga}_{1-x_1}\text{As}$ p			
114	$\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$ p+			
113	$\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$ und			
112	$\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$ N+			
111	$\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$ und			
110	GaAs und			
108	$\text{In}_{y_1}\text{Ga}_{1-y_1}\text{As}$ und			
109	GaAs und			
107	GaAs und			
106	$\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$ und			
105	$\text{Al}_{x_1}\text{Ga}_{1-x_1}\text{As}$ p			
104	GaAs p+			
103	AlAs und			
102	GaAs und			
101	AlAs und			
100	GaAs SI Substrate			

FIG. 1

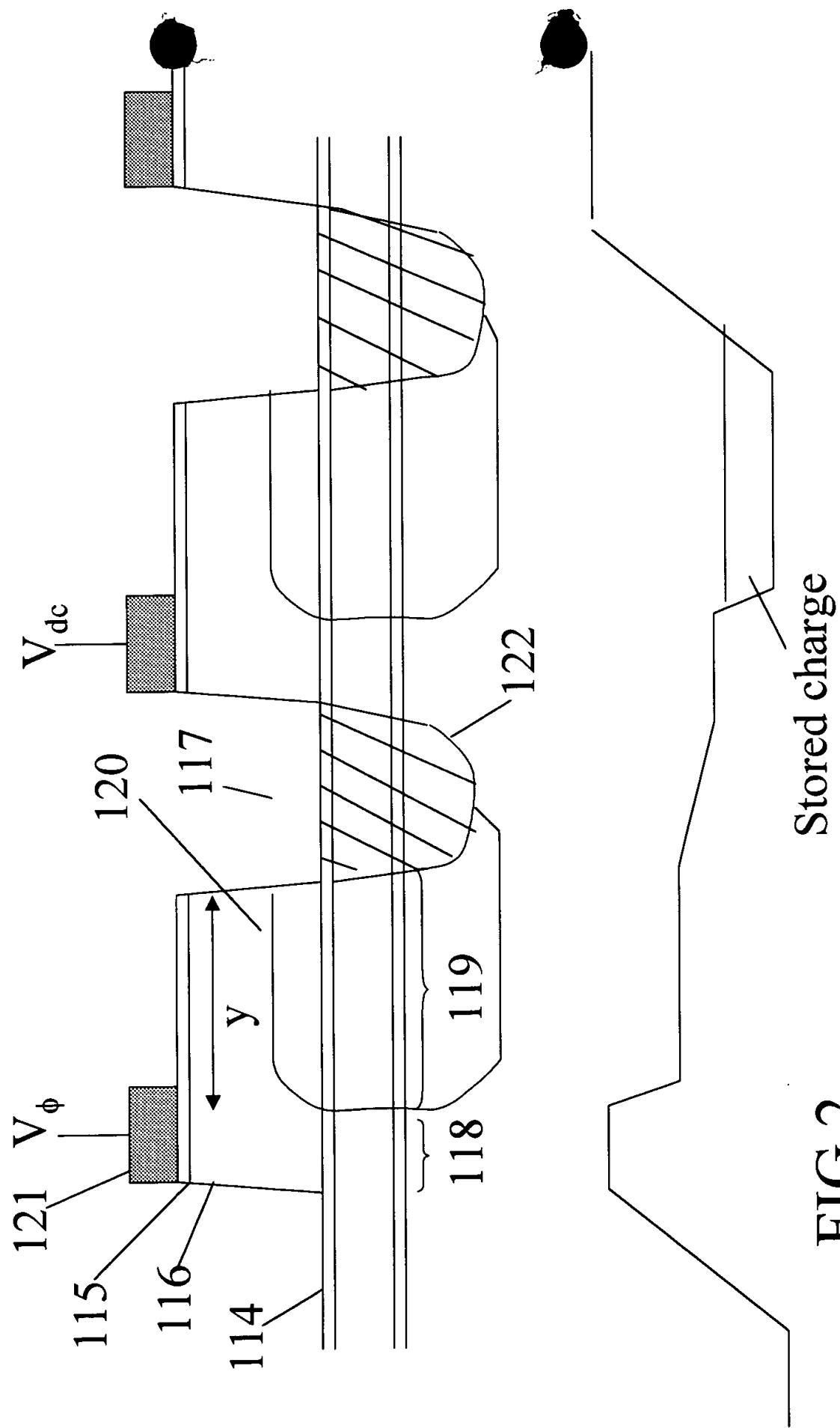


FIG.2

Stored charge

Intersubband Photocurrent  
(bound to continuum)

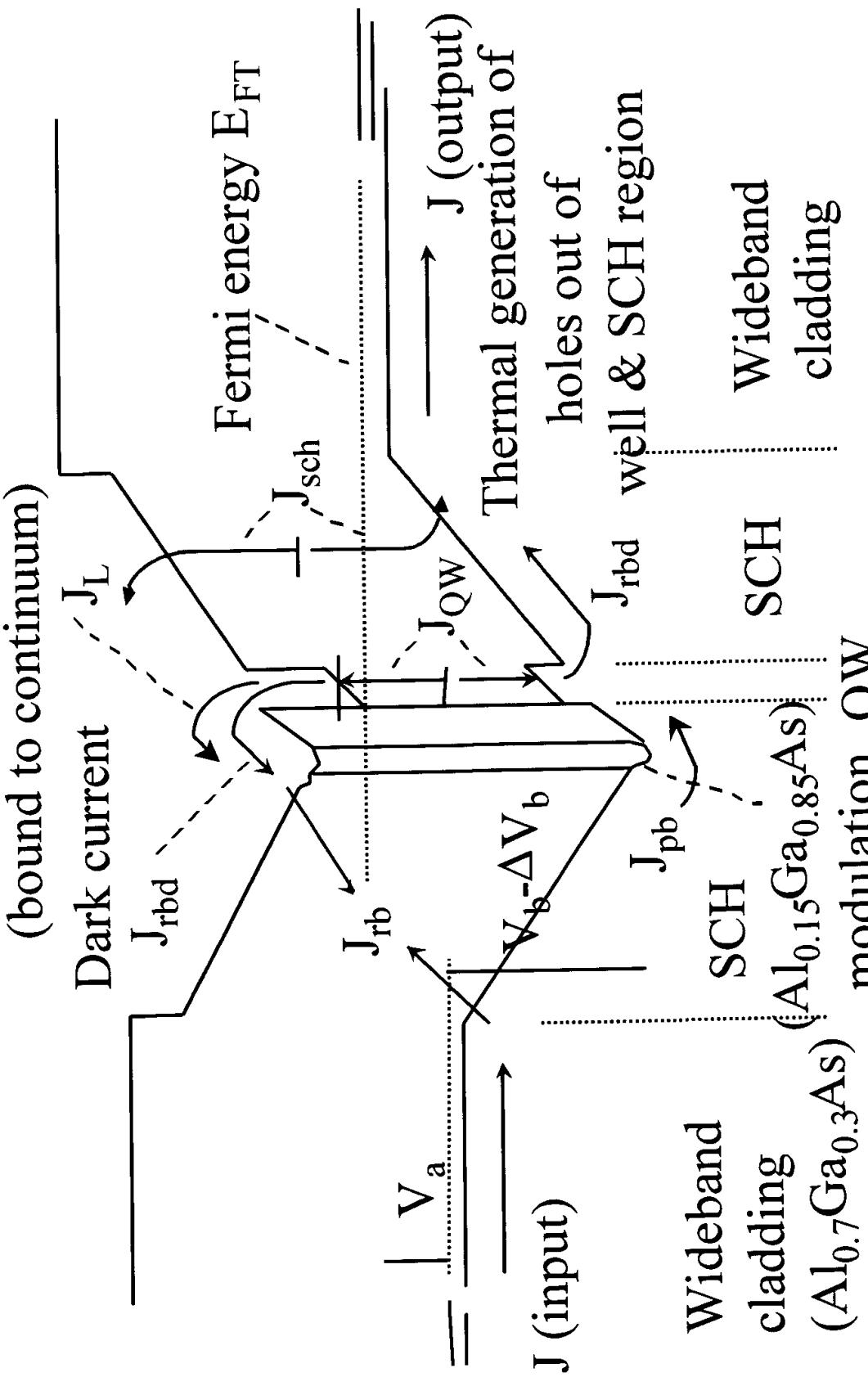


FIG.3  
Intersubband Photocurrent  
(bound to continuum)  
Wideband  
cladding  
( $\text{Al}_{0.7}\text{Ga}_{0.3}\text{As}$ )  
modulation QW  
doping

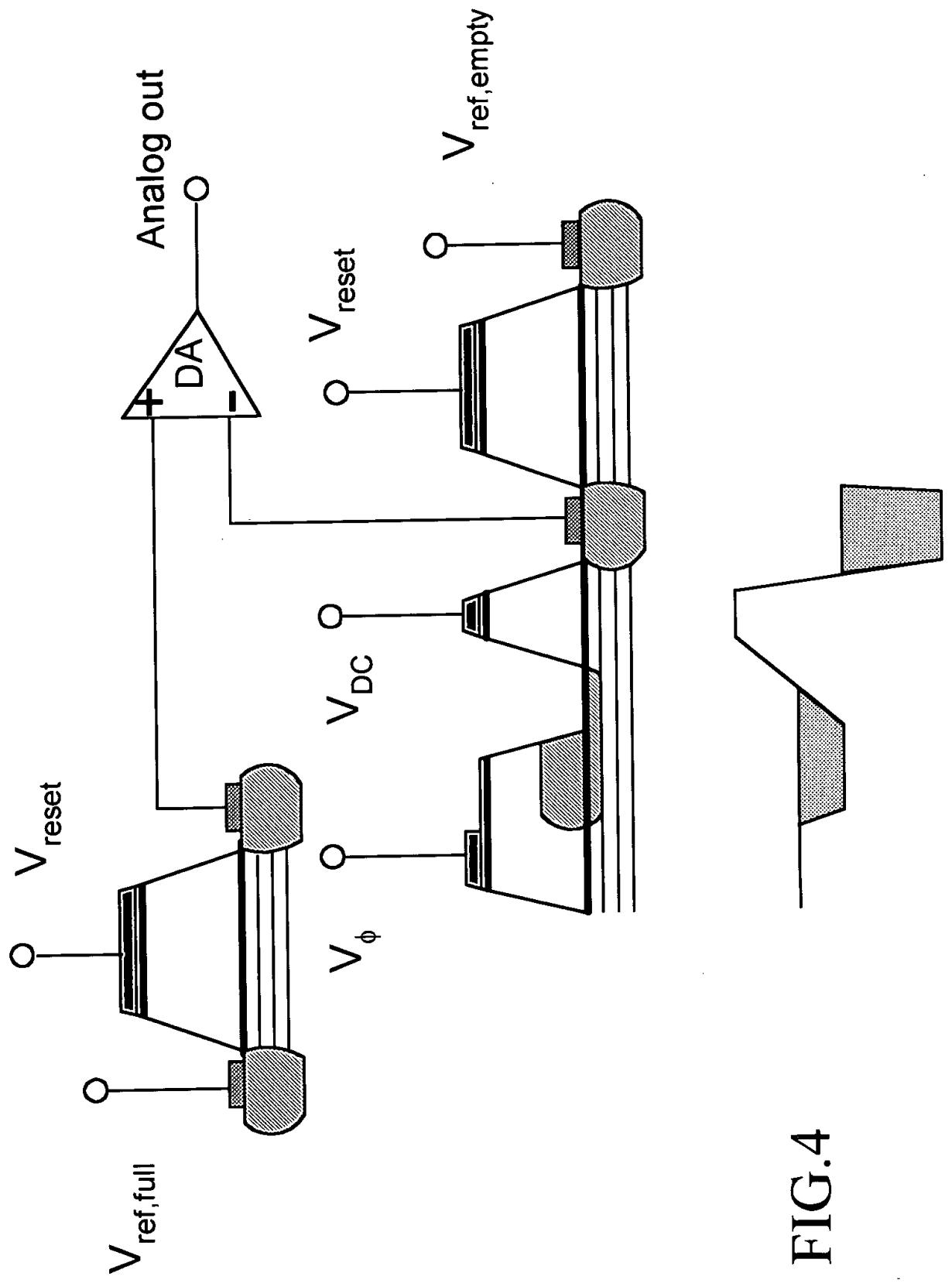


FIG.4